

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L12	2	((channel) near2 (tft or (thin adj film adj transistor))) near2 different near2 thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:12
L13	4	((channel) near3 (tft or (thin adj film adj transistor))) near3 different near3 thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:12
L14	159	((channel) near3 (tft or (thin adj film adj transistor))) near3 thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:12
L15	94	((channel) near2 (tft or (thin adj film adj transistor))) near2 thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:13
L16	15	((channel) near2 (tft or (thin adj film adj transistor))) near2 thickness).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:14
L17	1	((channel) near2 ((first or second) adj (tft or (thin adj film adj transistor)))) near2 thickness).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:14
L18	1	((channel) near2 ((first or second) adj (tft or (thin adj film adj transistor)))) near2 ((first or second) adj thickness)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:14
L19	1	((channel) near2 ((first or second) adj (tft or (thin adj film adj transistor)))) near2 ((first or second) adj thickness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:15
L20	1	((channel) near3 ((first or second) adj (tft or (thin adj film adj transistor)))) near3 ((first or second) adj thickness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:15

L21	1	((channel) near5 ((first or second) adj (tft or (thin adj film adj transistor)))) near5 ((first or second) adj thickness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:15
L22	2	((channel) near10 ((first or second) adj (tft or (thin adj film adj transistor)))) near5 ((first or second) adj thickness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:15
L23	2	((channel) near10 ((first or second) adj (tft or (thin adj film adj transistor)))) near10 ((first or second) adj thickness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:16
L24	10	((channel) near10 ((first or second) adj (tft or (thin adj film adj transistor)))) near10 thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:17
L25	10	((channel) near10 ((first or second) adj (tft or (thin adj film adj transistor)))) near10 (thicker or thick or thickness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:18
L26	10	((channel) with ((first or second) adj (tft or (thin adj film adj transistor)))) near10 (thicker or thick or thickness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:18
L27	21	((channel) with ((first or second) adj (tft or (thin adj film adj transistor)))) with (thicker or thick or thickness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:18
L28	334	(channel near (thicker))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:19
L29	720	(channel near2 (thicker))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:19
L30	65	(channel near2 (thicker)) and (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:19

L31	41	(channel near2 (thicker)) and (tft or (thin adj film adj transistor)).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:19
L32	23	(channel near2 (thicker)).ti,ab,clm. and (tft or (thin adj film adj transistor)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:25
L33	29	((first or second) near2 channel near2 (thick or thickness or thicker)).ti,ab,clm. and (tft or (thin adj film adj transistor)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:25
L34	9	((first or second) near2 channel near2 (thick or thickness or thicker)).ti,ab,clm. with (tft or (thin adj film adj transistor)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:26
L35	8	((first or second) near2 channel near2 (thick or thickness or thicker)) near10 (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:33
L36	146	(channel near2 ((varying or different or variable) adj thickness))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:37
L37	1	(channel near2 ((varying or different or variable) adj thickness)) near10 (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:34
L38	3	(channel near3 ((varying or different or variable) adj thickness)) near10 (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:35
L39	5	(channel near5 ((varying or different or variable) adj thickness)) near10 (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:36
L40	5	(channel near5 ((varying or different or variable) near thickness)) near10 (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:36

L41	8	(channel near5 ((varying or different or variable) near2 thickness)) near10 (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:37
L44	7786	(variable adj thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:38
L45	130	(variable adj thickness) and (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:38
L46	13	(variable adj thickness) and (tft or (thin adj film adj transistor)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:39
L47	1	channel near10 (variable adj thickness) and (tft or (thin adj film adj transistor)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:39
L48	1	channel with (variable adj thickness) and (tft or (thin adj film adj transistor)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:39
L49	35	(channel with ((varying or different or variable) adj thickness)) and (tft or (thin adj film adj transistor)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:41
L50	6	(channel with ((varying or different or variable) adj thickness)) and (((first or second) adj (tft or (thin adj film adj transistor)))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:42
L51	0	(channel with ((varying or different or variable) adj thickness)) with (((first or second) adj (tft or (thin adj film adj transistor)))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:42
L52	5	(channel with ((varying or different or variable) adj thickness)) with (((first or second) adj (tft or (thin adj film adj transistor)))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:43

L53	0	(channel near2 thicker) with ((first or second) adj (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:43
L54	2214	((first or second) adj (tft or (thin adj film adj transistor)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:43
L55	0	((first or second) adj (tft or (thin adj film adj transistor))) with (channel adj thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:43
L56	0	((first or second) adj (tft or (thin adj film adj transistor))) with (channel near thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:43
L57	2	((first or second) adj (tft or (thin adj film adj transistor))) with (channel near2 thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:44
L58	6	((first or second) adj (tft or (thin adj film adj transistor))) with (channel near5 thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:44
L59	11	(different adj channel adj thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:45
L60	12	((varying or variable or different) adj channel adj thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/19 19:46